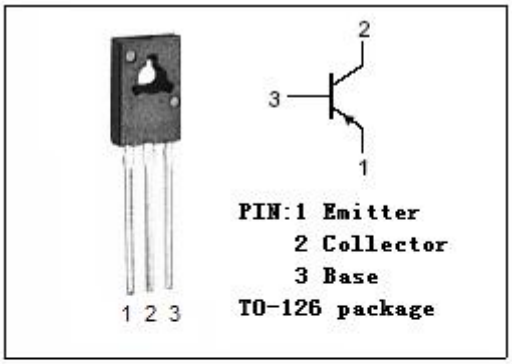
isc Silicon NPN Power Transistors — 2SB1261-K

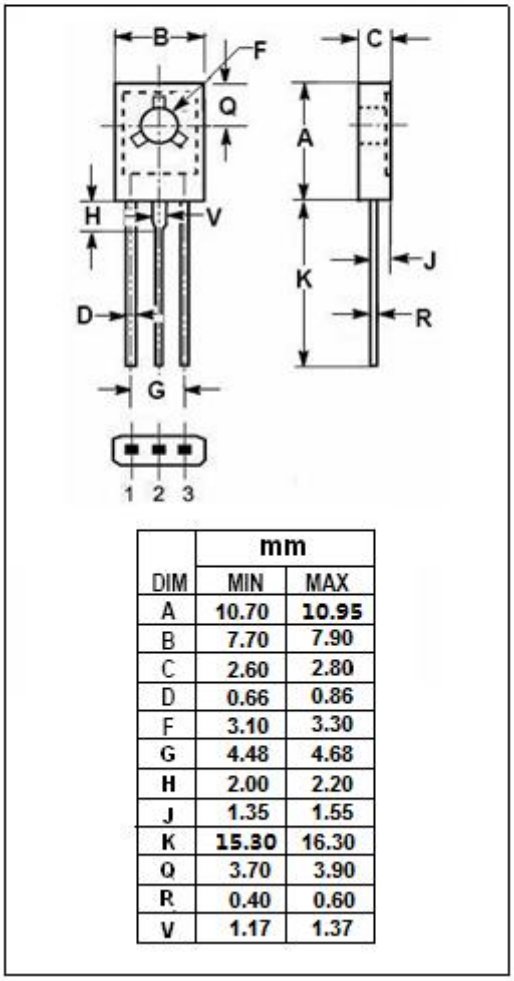


DESCRIPTION

- Low Collector Saturation Voltage
- High Power Dissipation-
  : P_C= 10W(Max)@T_C=25℃
- Complement to Type 2SD1899-K
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in audio amplifier and switching, especially in hybrid integrated circuits.



DIM	mm MIN	mm MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-3	A
P_C	Collector Power Dissipation @T_C=25℃	10	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -100 μ A ; I_E= 0	-60			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -1mA ; I_B= 0	-60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Vltage	I_E= -100 μ A; I_C= 0	-7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1.5A; I_B= -0.15A			-0.3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -1.5A; I_B= -0.15A			-1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -60V; I_E= 0			-10	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= -7V; I_C= 0			-10	μ A
h_{FE1}	DC Current Gain	I_C= -0.2A; V_{CE}= -2V	60			
h_{FE}	DC Current Gain	I_C= -0.6A; V_{CE}= -2V	200		400	
h_{FE}	DC Current Gain	I_C= -2A; V_{CE}= -2V	50			